

## T828N SERIES

### DISC TYPE THYRISTOR

#### Features

- Center amplifying gate
- Metal case with ceramic insulator
- tested according to IEC standards

828A

#### Typical Applications

- DC motor controls
- Controlled DC power supplies
- AC controllers

#### Major Ratings and Characteristics

Parameters	T828N	Units
$I_{T(AV)}$	828	A
@ $T_{hs}$	55	°C
$I_{T(RMS)}$	1324	A
@ $T_{hs}$	25	°C
$I_{TSM}$	@ 50Hz 7850	A
	@ 60Hz 8220	A
$I^2 t$	@ 50Hz 308	KA <sup>2</sup> s
	@ 60Hz 281	KA <sup>2</sup> s
$V_{DRM} / V_{RRM}$	1000 to 2000	V
$T_q$	typical 100	μs
$T_J$	range - 40 to 125	°C

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## ELECTRICAL SPECIFICATIONS

### Voltage Ratings

Type number	Voltage Code	$V_{RRM}$ , maximum repetitive peak reverse voltage V	$V_{RSM}$ , maximum non-repetitive peak rev. voltage V	$I_{RRM}$ max. @ $T_J = 125^\circ\text{C}$ mA
T828N	06	600	700	20
	08	800	900	
	10	1000	1100	
	12	1200	1300	
	14	1400	1500	
	16	1600	1700	

### On-state Conduction

Parameter	T828N	Units	Conditions		
$I_{T(AV)}$ Maximum average on-state current @ Heatsink temperature	828	A	180° conduction, half sine wave		
	55	°C	Double side(single side)cooled		
$I_{(RMS)}$ Maximum RMS on-state current	1324	A	DC@ 25°C heatsink temperature double side cooled		
$I_{TSM}$ Maximum peak, one-cycle non-repetitive surge current	7850	A	t = 10ms	No voltage	Sinusoidal half wave, Initial T = T max.
	8220		t = 8.3ms	reapplied	
	6600		t = 10ms	100% $V_{RRM}$	
	6900		t = 8.3ms	reapplied	
$I^2 t$ Maximum $I^2 t$ for fusing	308	KA <sup>2</sup> s	t = 10ms	No voltage	
	281		t = 8.3ms	reapplied	
	218		t = 10ms	100% $V_{RRM}$	
	200		t = 8.3ms	reapplied	
$I^2 \sqrt{t}$ Maximum $I^2 \sqrt{t}$ for fusing	3080	KA <sup>2</sup> √s	t = 0.1 to 10ms, no voltage reapplied		
$V_{TM}$ Maximum on-state or forward	1.36	V	$I_{pk} = 105A$ , $T_J = 125^\circ\text{C}$ , $t_p = 10\text{ms}$ sine pulse		
$I_H$ Maximum holding current	600	mA	$T_J = 25^\circ\text{C}$ , anode supply 12V resistive load		
$I_L$ Typical latching current	1000				

### Switching

Parameter	T828N	Units	Conditions
$di/dt$ Maximum non repetitive rate of rise of turned-on current	1000	A/μs	Gate drive 20V, 20Ω, $t_r \leq 1\mu\text{s}$ $T_J = T_J \text{ max}$ , anode voltage $\leq 80\% V_{DRM}$
$t_d$ Typical delay time	1.0	μs	Gate current 1A, $dig/dt = 1A/\mu\text{s}$ $V_d = 0.67\% V_{DRM}$ , $T_J = 25^\circ\text{C}$
$T_q$ Typical turn-off time	100	A/μs	$I_{TM} = 300A$ , $T_J = T_J \text{ max}$ , $di/dt = 20A/\mu\text{s}$ , $V_R = 50V$ $dv/dt = 20V/\mu\text{s}$ , Gate 0V 100Ω, $t_p = 500\mu\text{s}$

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### Blocking

Parameter	T828N	Units	Conditions
dv/dt Maximum critical rate of rise of off-state voltage	500	V/ $\mu$ s	T <sub>J</sub> = T <sub>J</sub> max linear to 80% rated V <sub>DRM</sub>
I <sub>DRM</sub> Max. peak reverse and off-state leakage current	30	mA	T <sub>J</sub> = T <sub>J</sub> max, rated V <sub>DRM</sub> /V <sub>RRM</sub> applied

### Triggering

Parameter	T828N	Units	Conditions
P <sub>GM</sub> Maximum peak gate power	10	W	T <sub>J</sub> = T <sub>J</sub> max, t <sub>p</sub> ≤ 5ms
P <sub>G(AV)</sub> Maximum average gate power	2.0		T <sub>J</sub> = T <sub>J</sub> max, f = 50Hz, d% = 50
I <sub>GM</sub> Max. peak positive gate current	3.0	A	T <sub>J</sub> = T <sub>J</sub> max, t <sub>p</sub> ≤ 5ms
+V <sub>GM</sub> Maximum peak positive gate voltage	20	V	T <sub>J</sub> = T <sub>J</sub> max, t <sub>p</sub> ≤ 5ms
-V <sub>GM</sub> Maximum peak negative gate voltage	5.0		
I <sub>GT</sub> DC gate current required to trigger	TYP.	MAX.	T <sub>J</sub> = -40°C T <sub>J</sub> = 25°C T <sub>J</sub> = 125°C Max. required gate trigger/ current/ voltage are the lowest value which will trigger all units 12V anode-to-cathode applied
	180	-	
	90	150	
V <sub>GT</sub> DC gate voltage required to trigger	2.9	-	T <sub>J</sub> = -40°C T <sub>J</sub> = 25°C T <sub>J</sub> = 125°C
	1.8	30	
	1.2	-	
I <sub>GD</sub> DC gate current not to trigger	10	mA	T <sub>J</sub> = T <sub>J</sub> max Max. gate current/ voltage not to trigger is the max. value which will not trigger any unit with rated V anode-to-cathode applied
V <sub>GD</sub> DC gate voltage not to trigger	0.30	V	

### Thermal and Mechanical Specification

Parameter	T828N	Units	Conditions
T <sub>J</sub> Max. operating temperature range	-40 to 125	°C	
T <sub>stg</sub> Max. storage temperature range	-40 to 150		
R <sub>thJC</sub> Max. thermal resistance, junction to case	0.17 0.08	K/W	DC operation
R <sub>thCS</sub> Max. thermal resistance, case to heatsink	0.033 0.017		Mounting surface, smooth, flat and greased
T Mounting torque, ± 10%	4900 (500)		
wt Approximate weight	110	g	

Outline Table

